

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI MRF340** is Designed for VHF Radios that use Collector Modulation in the Driver/Final Amplifiers to Produce an Amplitude Modulated Signal.

FEATURES INCLUDE:

- Replaces Original **MRF340** in Most Applications
- High Gain Reduces Drive Requirements
- Economical **TO-220CE** Package

MAXIMUM RATINGS

I_C	1.0 A
V_{CES}	50 V
P_{DISS}	12.5 W @ T _C = 25 °C
T_{STG}	-55 °C to +150 °C
θ_{JC}	10 °C/W

PACKAGE STYLE TO-220AB (COMMON EMITTER)

1 = BASE 2 = EMITTER
3 = COLLECTOR TAB = EMITTER

	DIMENSIONS			
	mm		inches	
	min	max	min	max
A	10	10.4	0.393	0.409
B	15.2	15.9	0.598	0.626
C	12.7	13.7	0.500	0.539
D	6.2	6.6	0.244	0.260
E	4.4	4.6	0.173	0.181
F	3.5	5.5	0.137	0.216
G	2.65	2.95	0.104	0.116
H	17.6 typ.		0.692 typ.	
L	1.14	1.7	0.044	0.067
M	3.75	3.85	0.147	0.151
N	1.23	1.32	0.048	0.051
P	0.41	0.64	0.016	0.025
R	2.4	2.72	0.094	0.107
S	4.95	5.15	0.194	0.203
T	2.4	2.7	0.094	0.106
U	0.61	0.94	0.024	0.037

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	I _C = 50 mA			50			V
BV_{CBO}	I _C = 10 mA			50			V
BV_{EBO}	I _E = 5.0mA			4.0			V
I_{CES}	V _{CES} = 25V					1.0	mA
h_{FE}	V _{CE} = 10V	I _C = 100mA		10		200	---
C_{OB}	V _{CB} = 30 V	f = 1.0 MHz			15		pF
G_{PE}	V _{CC} = 13.5V	P _{out} = 2.0 W	f = 136 MHz		10		dB
G_{PE} η	V _{CC} = 27 V	P _{out} = 8.0 W _{pk}	f = 136 MHz	13.0	15.0		dB %